**Product data sheet** 

# 1. General description

Dual ultrafast power diode in a SOT78 (TO-220AB) plastic package.

## 2. Features and benefits

- Fast switching
- Low thermal resistance
- High thermal cycling performance
- Very low forward voltage drop
- High reverse surge capability
- Soft recovery characteristic

## 3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage		200				V
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; $T_{mb} \le 114$ °C; SQW; Fig. 1; Fig. 2; Fig. 3		15			А
$I_{O(AV)}$	average output current	$\delta$ = 0.5; T <sub>mb</sub> ≤ 114 °C; SQW; both diodes conducting	30			А	
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode; Fig. 4	150				А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	165				Α
$V_{ESD}$	electrostatic discharge voltage	HBM; all pins; C =250 pF; R = 1.5 k $\Omega$	8			kV	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics		·				
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	0.95	1.05	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1	1.2	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	- 0.78 0.85			0.85	V
Dynamic	characteristics	'					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ - 18 25 $T_i = 25 \text{ °C}; \text{ ramp recovery; } \frac{\text{Fig. 7}}{\text{C}}$				25	ns

**Dual ultrafast power diode** 

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode		M N M
3	A2	anode 2		A1 A2
mb	K	mounting base; cathode		K sym125
			1 2 3	

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BYQ42E-200	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking codes
BYQ42E-200	BYQ42E-200

**Dual ultrafast power diode** 

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		200	V
$V_{RWM}$	crest working reverse voltage		200	V
$V_R$	reverse voltage	DC	200	V
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; $T_{mb} \le 114$ °C; SQW; Fig. 1; Fig. 2; Fig. 3	15	А
I <sub>O(AV)</sub>	average output current	δ = 0.5; T <sub>mb</sub> ≤ 114 °C; SQW; both diodes conducting	30	А
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode; Fig. 4	150	А
	forward current	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	165	А
I <sub>RRM</sub>	repetitive peak reverse current	$\delta$ = 0.001; $t_p$ = 2 $\mu$ s	0.2	А
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs	0.2	А
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		150	°C
Electrosta	tic discharge			1
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = 1.5 kΩ	8	kV

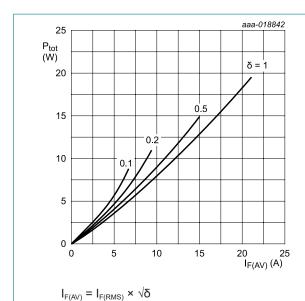


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

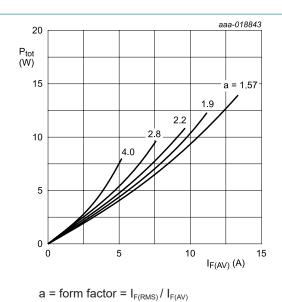


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

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## **Dual ultrafast power diode**

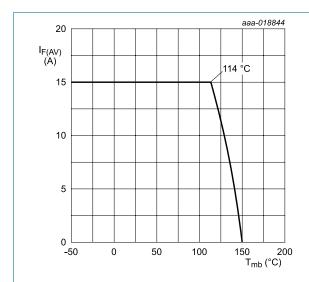


Fig. 3. Average forward current as a function of mounting base temperature; per diode; maximum values

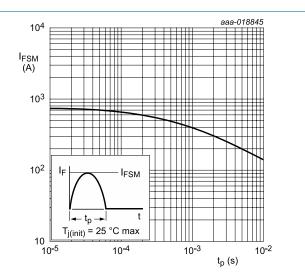


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; per diode; maximum values

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**Dual ultrafast power diode** 

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to	with heatsink compound; both diodes conducting	-	-	1.4	K/W
	mounting base	with heatsink compound; per diode; <u>Fig. 5</u>	-	-	2.4	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air		-	60	-	K/W

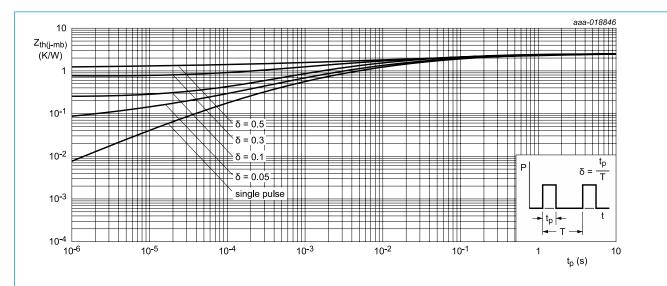
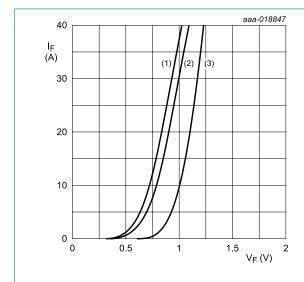


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; per diode; maximum values

## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	0.78	0.85	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	0.95	1.05	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1	1.2	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C	-	3	20	μA
		V <sub>R</sub> = 200 V; T <sub>j</sub> = 150 °C	-	0.3	1	mA
Dynamic	characteristics					
$Q_r$	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	6	15	nC
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	10	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ ramp recovery; $T_j = 25 \text{ °C}; Fig. 7$	-	18	25	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	1	-	V



 $V_{\rm O}$  = 0.712 V; R<sub>S</sub> = 0.009  $\Omega$  (1) T<sub>i</sub> = 150 °C; typical values

(2)  $T_j = 150$  °C; maximum values

(3)  $T_j = 25$  °C; maximum values Fig. 6. Forward current as a function of forward

voltage; per diode

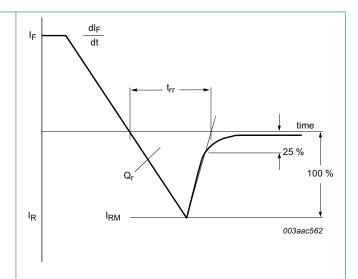


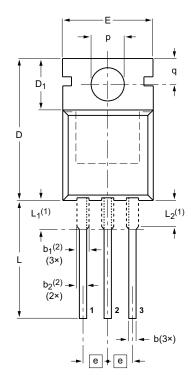
Fig. 7. Reverse recovery definitions; ramp recovery

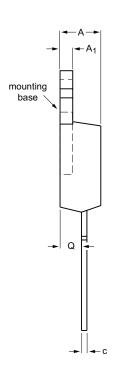
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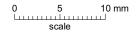
# 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

**SOT78** 







### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

### Notes

- ${\it 1. Lead shoulder designs may vary.}\\$
- 2. Dimension includes excess dambar.

OUTLIN	JTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	N	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78	3		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

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### **Dual ultrafast power diode**

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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